

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI VHB10-28F is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	1.0 A
<b>V<sub>CB0</sub></b>	65 V
<b>V<sub>CEO</sub></b>	35 V
<b>V<sub>CES</sub></b>	65 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	13.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	5.5 °C/W

**PACKAGE STYLE .380 4L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

**ORDER CODE: ASI10721**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 200 mA	65			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 200 mA	65			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 200 mA	35			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 30 V			1.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 200 mA	5.0		---	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz			15	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 28 V      P <sub>OUT</sub> = 10 W      f = 175 MHz	10			<b>dB</b>
<b>η<sub>C</sub></b>			60		<b>%</b>